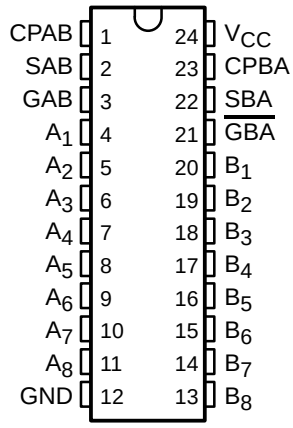
- **Function, Pinout, and Drive Compatible With FCT and F Logic**
- **Reduced V_{OH} (Typically = 3.3 V) Version of Equivalent FCT Functions**
- **Edge-Rate Control Circuitry for Significantly Improved Noise Characteristics**
- **I_{off} Supports Partial-Power-Down Mode Operation**
- **Matched Rise and Fall Times**
- **Fully Compatible With TTL Input and Output Logic Levels**
- **64-mA Output Sink Current 32-mA Output Source Current**
- **Independent Register for A and B Buses**
- **Multiplexed Real-Time and Stored Data Transfer**
- **3-State Outputs**

Q OR SO PACKAGE
(TOP VIEW)



description

The CY74FCT652T consists of bus transceiver circuits, D-type flip-flops, and control circuitry arranged for multiplexed transmission of data directly from the input bus or from the internal storage registers. GAB and $\overline{GBA}$ inputs control the transceiver functions. Select-control (SAB and SBA) inputs select either real-time or stored-data transfer. The circuitry used for select control eliminates the typical decoding glitch that occurs in a multiplexer during the transition between stored and real-time data. A low input level selects real-time data, and a high input level selects stored data.

Data on the A or B data bus, or both, can be stored in the internal D-type flip-flops by low-to-high transitions of the appropriate clock (CPAB or CPBA) inputs, regardless of the select or enable levels of the control pins. When SAB and SBA are in the real-time transfer mode, it also is possible to store data without using the internal D-type flip-flops by simultaneously enabling GAB and $\overline{GBA}$. In this configuration, each output reinforces its input. Thus, when all other data sources to the two sets of bus lines are at high impedance, each set of bus lines remains at its last state.

This device is fully specified for partial-power-down applications using I_{off}. The I_{off} circuitry disables the outputs, preventing damaging current backflow through the device when it is powered down.

ORDERING INFORMATION

T_A	PACKAGE†		SPEED (ns)	ORDERABLE PART NUMBER	TOP-SIDE MARKING
–40°C to 85°C	QSOP – Q	Tape and reel	5.4	CY74FCT652CTQCT	FCT652C
	SOIC – SO	Tube	5.4	CY74FCT652CTSOC	FCT652C
		Tape and reel	5.4	CY74FCT652CTSOCT	
	QSOP – Q	Tape and reel	6.3	CY74FCT652ATQCT	FCT652A
	SOIC – SO	Tube	6.3	CY74FCT652ATSOC	FCT652A
		Tape and reel	6.3	CY74FCT652ATSOCT	
	QSOP – Q	Tape and reel	9	CY74FCT652TQCT	FCT652

† Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

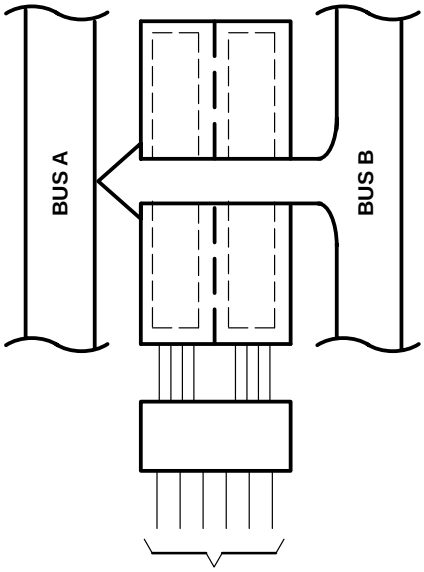
FUNCTION TABLE

INPUTS						DATA I/O		OPERATION OR FUNCTION
GAB	$\overline{GBA}$	CPAB	CPBA	SAB	SBA	A_1–A_8	B_1–B_8	
L	H	H or L	H or L	X	X	Input	Input	Isolation
L	H	↑	↑	X	X	Input	Input	Store A and B data
X	H	↑	H or L	X	X	Input	Unspecified§	Store A, hold B
H	H	↑	↑	X‡	X	Input	Output	Store A in both registers
L	X	H or L	↑	X	X	Unspecified§	Input	Hold A, store B
L	L	↑	↑	X	X‡	Output	Input	Store B in both registers
L	L	X	X	X	L	Output	Input	Real-time B data to A bus
L	L	X	H or L	X	H	Output	Input	Stored B data to A bus
H	H	X	X	L	X	Input	Output	Real-time A data to B bus
H	H	H or L	X	H	X	Input	Output	Stored A data to B bus
H	L	H or L	H or L	H	H	Output	Output	Stored A data to B bus and Stored B data to A bus

H = High logic level, L = Low logic level, X = Don't care, ↑ = Low-to-high transition

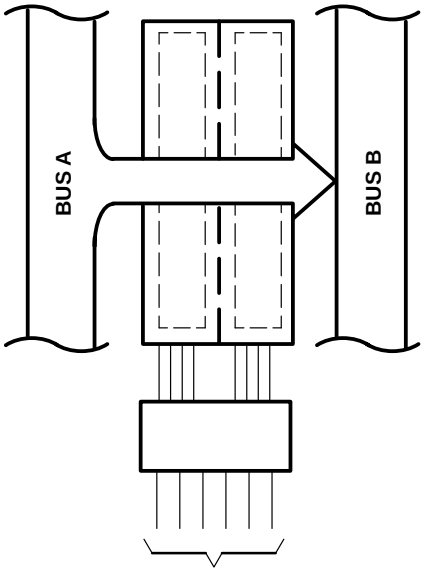
‡ Select control = L: clocks can occur simultaneously. Select control = H: clocks must be staggered in order to load both registers.

§ The data output functions can be enabled or disabled by various signals at the GAB and $\overline{GBA}$ inputs. Data input functions always are enabled, i.e., data at the bus pins are stored on every low-to-high transition of the clock inputs.



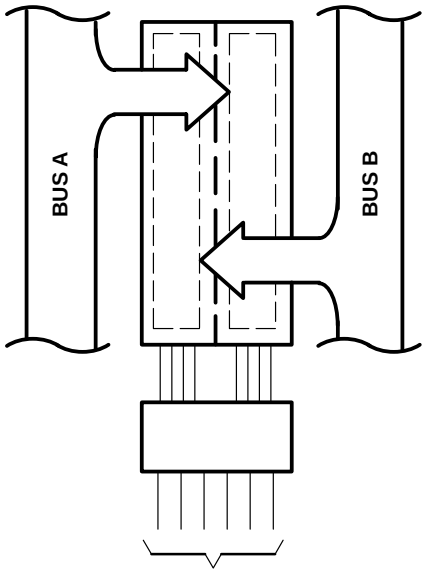
3	21	1	23	2	22
GAB	$\overline{GBA}$	CPAB	CPBA	SAB	SBA
L	L	X	X	X	L

REAL-TIME TRANSFER
BUS B TO BUS A



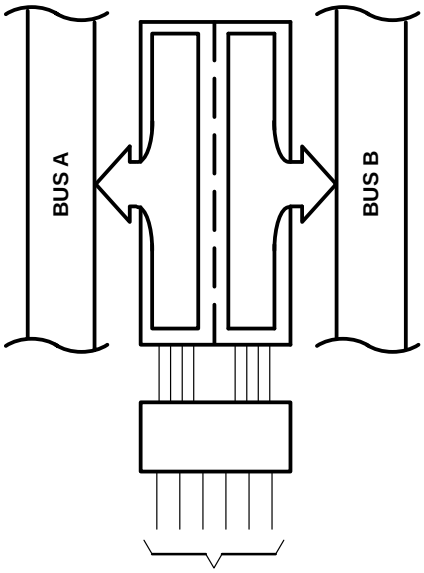
3	21	1	23	2	22
GAB	$\overline{GBA}$	CPAB	CPBA	SAB	SBA
H	H	X	X	L	X

REAL-TIME TRANSFER
BUS A TO BUS B



3	21	1	23	2	22
GAB	$\overline{GBA}$	CPAB	CPBA	SAB	SBA
X	H	↑	X	X	X
L	X	X	↑	X	X
L	H	↑	↑	X	X

STORE DATA
FROM A AND/OR B

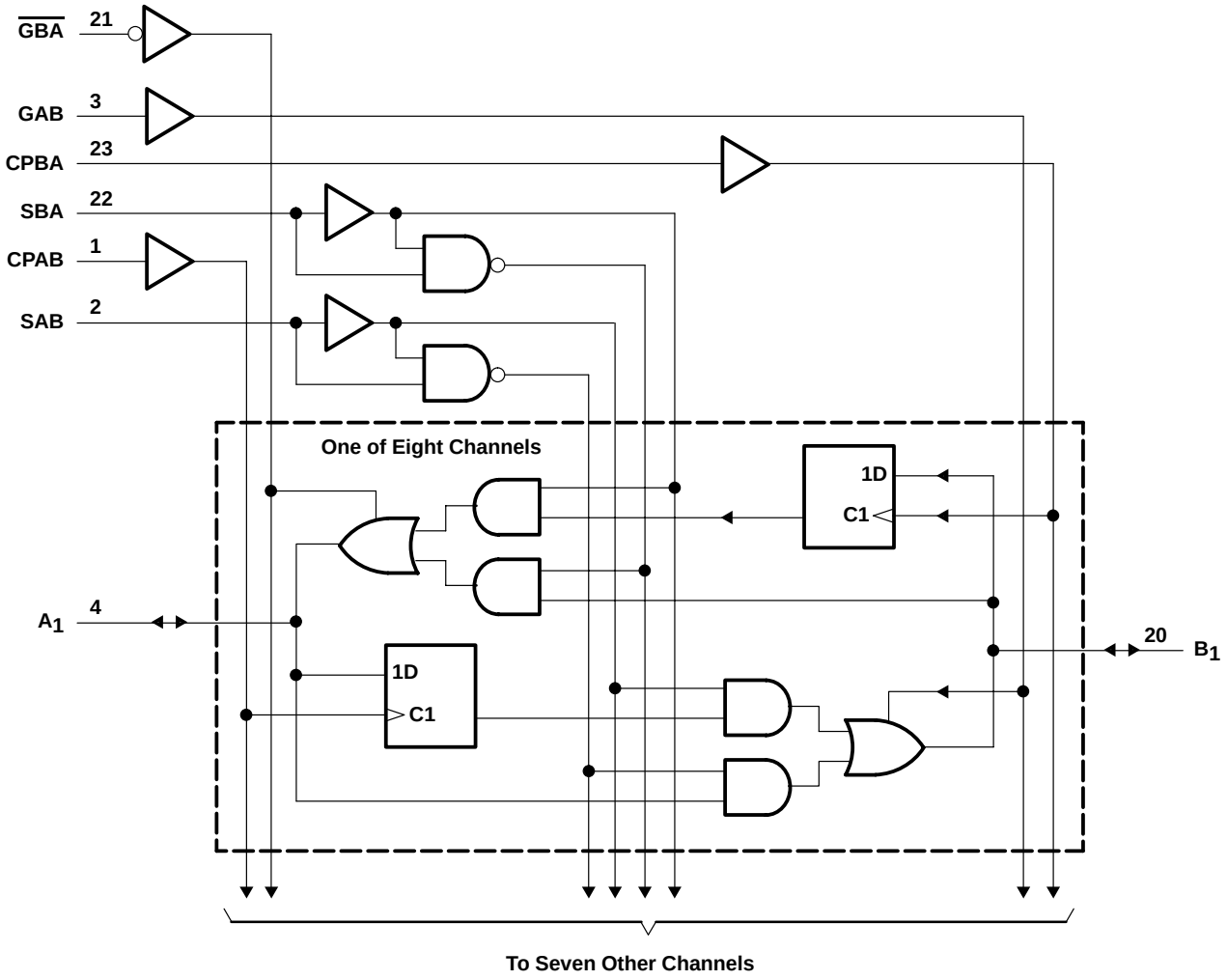


3	21	1	23	2	22
GAB	$\overline{GBA}$	CPAB	CPBA	SAB	SBA
H	L	H or L	H or L	H	H

TRANSFER STORED DATA
TO A AND/OR B

Figure 1. Bus-Management Functions

logic diagram (positive logic)



absolute maximum ratings over operating free-air temperature range (unless otherwise noted)†

Supply voltage range to ground potential . . . . . –0.5 V to 7 V
DC input voltage range . . . . . –0.5 V to 7 V
DC output voltage range . . . . . –0.5 V to 7 V
DC output current (maximum sink current/pin) . . . . . 120 mA
Package thermal impedance, θ_{JA} (see Note 1): Q package . . . . . 61°C/W
SO package . . . . . 46°C/W
Ambient temperature range with power applied, T_A . . . . . –65°C to 135°C
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions (see Note 2)

		MIN	NOM	MAX	UNIT
V_{CC}	Supply voltage	4.75	5	5.25	V
V_{IH}	High-level input voltage	2			V
V_{IL}	Low-level input voltage			0.8	V
I_{OH}	High-level output current			–32	mA
I_{OL}	Low-level output current			64	mA
T_A	Operating free-air temperature	–40		85	°C

NOTE 2: All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation.

electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS			MIN	TYP†	MAX	UNIT
V_{IK}	V_{CC} = 4.75 V,	I_{IN} = –18 mA			–0.7	–1.2	V
V_{OH}	V_{CC} = 4.75 V	I_{OH} = –32 mA		2			V
		I_{OH} = –15 mA		2.4	3.3		
V_{OL}	V_{CC} = 4.75 V,	I_{OL} = 64 mA			0.3	0.55	V
V_{hys}	All inputs				0.2		V
I_I	V_{CC} = 5.25 V,	V_{IN} = V_{CC}				5	µA
I_{IH}	V_{CC} = 5.25 V,	V_{IN} = 2.7 V				±1	µA
I_{IL}	V_{CC} = 5.25 V,	V_{IN} = 0.5 V				±1	µA
I_{OZH}	V_{CC} = 5.25 V,	V_{OUT} = 2.7 V				10	µA
I_{OZL}	V_{CC} = 5.25 V,	V_{OUT} = 0.5 V				–10	µA
I_{OS}‡	V_{CC} = 5.25 V,	V_{OUT} = 0 V		–60	–120	–225	mA
I_{off}	V_{CC} = 0 V,	V_{OUT} = 4.5 V				±1	µA
I_{CC}	V_{CC} = 5.25 V,	V_{IN} ≤ 0.2 V,	V_{IN} ≥ V_{CC} – 0.2 V		0.1	0.2	mA
ΔI_{CC}	V_{CC} = 5.25 V, V_{IN} = 3.4 V§, f_1 = 0, Outputs open				0.5	2	mA
I_{CCD}¶	V_{CC} = 5.25 V, One input switching at 50% duty cycle, Outputs open, GAB or $\overline{GBA}$ = GND, V_{IN} ≤ 0.2 V or V_{IN} ≥ V_{CC} – 0.2 V				0.06	0.12	mA/ MHz
I_C#	V_{CC} = 5.25 V, f_0 = 10 MHz, Outputs $\overline{open}$, GAB = $\overline{GBA}$ = GND, SAB = CPAB = GND, SBA = V_{CC}	One bit switching at f_1 = 5 MHz at 50% duty cycle	V_{IN} ≤ 0.2 V or V_{IN} ≥ V_{CC} – 0.2 V		0.7	1.4	mA
			V_{IN} = 3.4 V or GND		1.2	3.4	
		Eight bits switching at f_1 = 5 MHz at 50% duty cycle	V_{IN} ≤ 0.2 V or V_{IN} ≥ V_{CC} – 0.2 V		2.8	5.6‖	
			V_{IN} = 3.4 V or GND		5.1	14.6‖	
C_i					5	10	pF
C_o					9	12	pF

† Typical values are at V_{CC} = 5 V, T_A = 25°C.

‡ Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high-speed test apparatus and/or sample-and-hold techniques are preferable to minimize internal chip heating and more accurately reflect operational values. Otherwise, prolonged shorting of a high output can raise the chip temperature well above normal and cause invalid readings in other parametric tests. In any sequence of parameter tests, I_{OS} tests should be performed last.

§ Per TTL-driven input (V_{IN} = 3.4 V); all other inputs at V_{CC} or GND

¶ This parameter is derived for use in total power-supply calculations.

$I_C = I_{CC} + \Delta I_{CC} \times D_H \times N_T + I_{CCD} (f_0/2 + f_1 \times N_1)$

Where:

I_C = Total supply current
I_{CC} = Power-supply current with CMOS input levels
ΔI_{CC} = Power-supply current for a TTL high input (V_{IN} = 3.4 V)
D_H = Duty cycle for TTL inputs high
N_T = Number of TTL inputs at D_H
I_{CCD} = Dynamic current caused by an input transition pair (HLH or LHL)
f_0 = Clock frequency for registered devices, otherwise zero
f_1 = Input signal frequency
N_1 = Number of inputs changing at f_1

All currents are in milliamperes and all frequencies are in megahertz.

‖ Values for these conditions are examples of the I_{CC} formula.

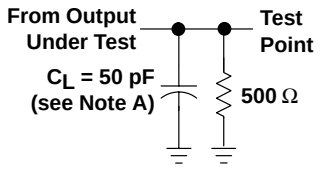
timing requirements over recommended operating free-air temperature range (unless otherwise noted) (see Figure 2)

			CY74FCT652T		CY74FCT652AT		CY74FCT652CT		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_w	Pulse duration, clock high or low		6		5		5		ns
t_{su}	Setup time, before CPAB↑ or CPBA↑	A or B	4		2		2		ns
t_h	Hold time, after CPAB↑ or CPBA↑	A or B	2		1.5		1.5		ns

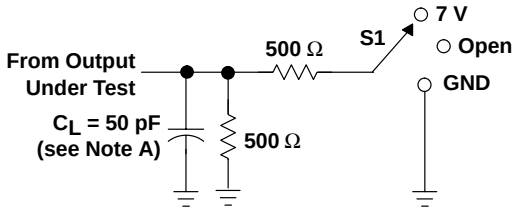
switching characteristics over operating free-air temperature range (see Figure 2)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	CY74FCT652T		CY74FCT652AT		CY74FCT652CT		UNIT
			MIN	MAX	MIN	MAX	MIN	MAX	
t_{PLH}	A or B	B or A	1.5	9	1.5	6.3	1.5	5.4	ns
t_{PHL}			1.5	9	1.5	6.3	1.5	5.4	
t_{PZH}	GAB or $\overline{GBA}$	A or B	1.5	14	1.5	9.8	1.5	7.8	ns
t_{PZL}			1.5	14	1.5	9.8	1.5	7.8	
t_{PHZ}	GAB or $\overline{GBA}$	A or B	1.5	9	1.5	6.3	1.5	6.3	ns
t_{PLZ}			1.5	9	1.5	6.3	1.5	6.3	
t_{PLH}	CPAB or CPBA	A or B	1.5	9	1.5	6.3	1.5	5.7	ns
t_{PHL}			1.5	9	1.5	6.3	1.5	5.7	
t_{PLH}	SBA or SAB	A or B	1.5	11	1.5	7.7	1.5	6.2	ns
t_{PHL}			1.5	11	1.5	7.7	1.5	6.2	

PARAMETER MEASUREMENT INFORMATION

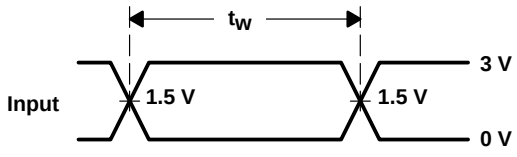


LOAD CIRCUIT FOR
TOTEM-POLE OUTPUTS

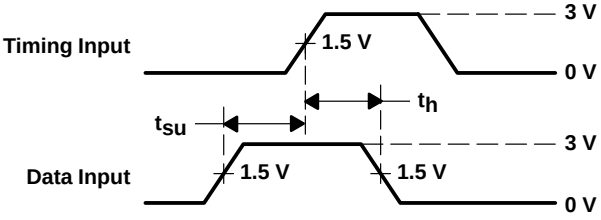


LOAD CIRCUIT FOR
3-STATE OUTPUTS

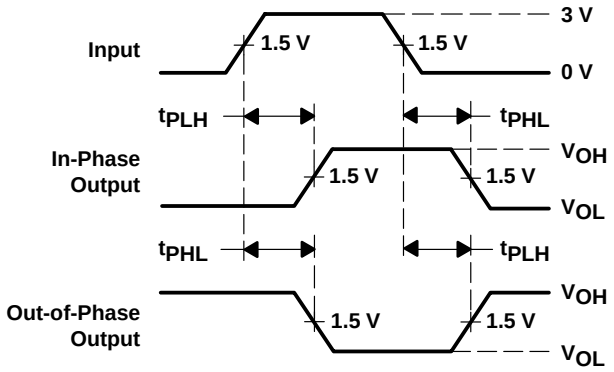
TEST	S1
t_{PLH}/t_{PHL}	Open
t_{PLZ}/t_{PZL}	7 V
t_{PHZ}/t_{PZH}	Open



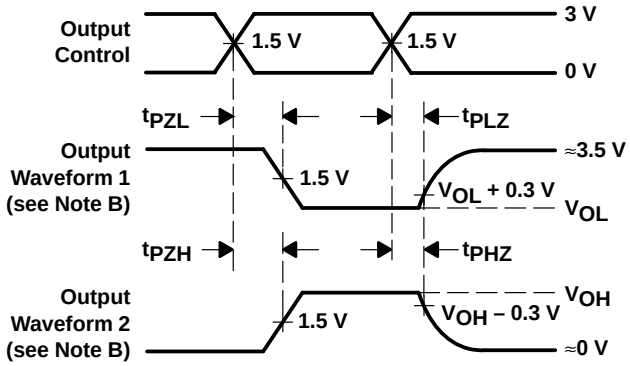
VOLTAGE WAVEFORMS
PULSE DURATION



VOLTAGE WAVEFORMS
SETUP AND HOLD TIMES



VOLTAGE WAVEFORMS
PROPAGATION DELAY TIMES
INVERTING AND NONINVERTING OUTPUTS



VOLTAGE WAVEFORMS
ENABLE AND DISABLE TIMES
LOW- AND HIGH-LEVEL ENABLING

NOTES: A. C_L includes probe and jig capacitance.
B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
C. The outputs are measured one at a time with one input transition per measurement.

Figure 2. Load Circuit and Voltage Waveforms

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package | Pins	Package qty | Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
CY74FCT652ATQCT	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT652A
CY74FCT652ATQCT.B	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT652A
CY74FCT652ATSOC	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT652A
CY74FCT652ATSOC.B	Active	Production	SOIC (DW) | 24	25 | TUBE	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT652A
CY74FCT652ATSOCT	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT652A
CY74FCT652ATSOCT.B	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT652A
CY74FCT652CTQCT	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT652C
CY74FCT652CTQCT.B	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT652C
CY74FCT652CTQCTG4.B	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT652C
CY74FCT652CTSOCT	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT652C
CY74FCT652CTSOCT.B	Active	Production	SOIC (DW) | 24	2000 | LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 85	FCT652C
CY74FCT652TQCT	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT652
CY74FCT652TQCT.B	Active	Production	SSOP (DBQ) | 24	2500 | LARGE T&R	Yes	NIPDAU	Level-2-260C-1 YEAR	-40 to 85	FCT652

(1) **Status:** For more details on status, see our product life cycle.

(2) **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

(3) **RoHS values:** Yes, No, RoHS Exempt. See the TI RoHS Statement for additional information and value definition.

(4) **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

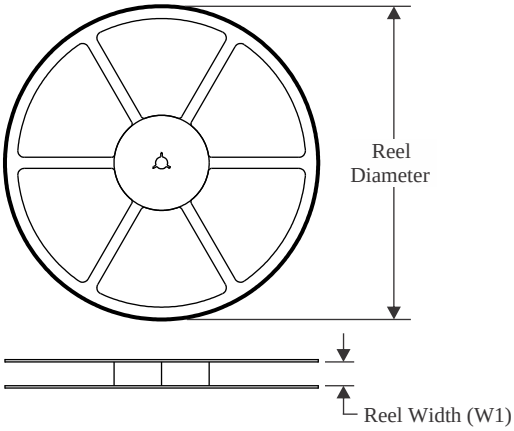
(5) **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

(6) **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

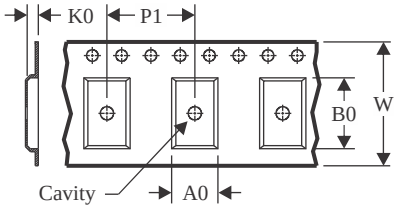
Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

TAPE AND REEL INFORMATION

REEL DIMENSIONS

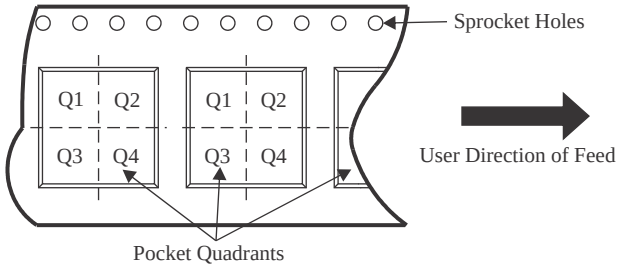


TAPE DIMENSIONS



A0	Dimension designed to accommodate the component width
B0	Dimension designed to accommodate the component length
K0	Dimension designed to accommodate the component thickness
W	Overall width of the carrier tape
P1	Pitch between successive cavity centers

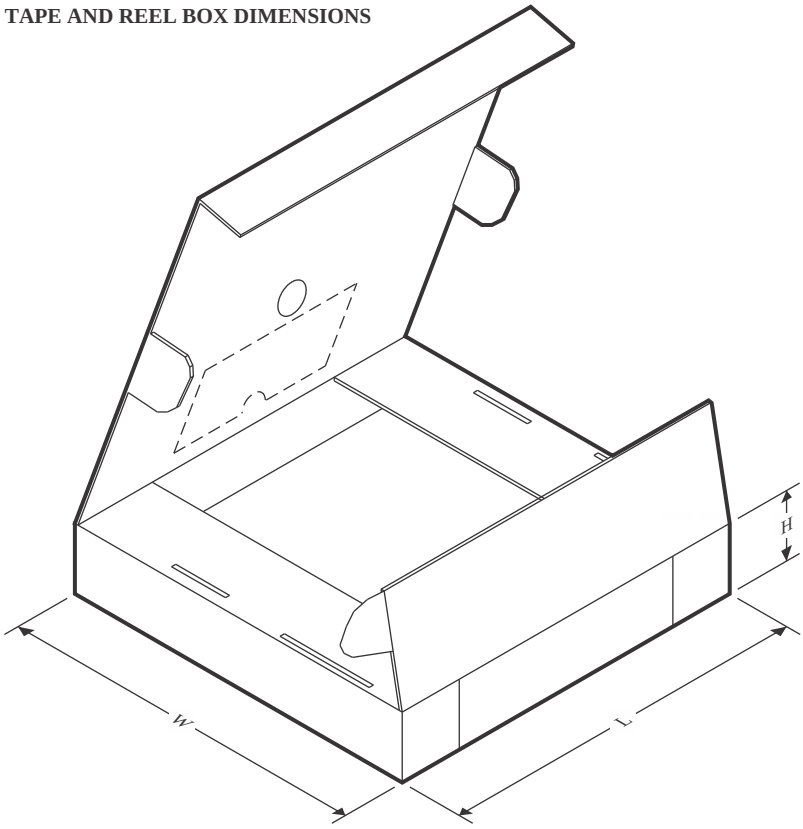
QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CY74FCT652ATQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT652ATSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CY74FCT652CTQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1
CY74FCT652CTSOCT	SOIC	DW	24	2000	330.0	24.4	10.75	15.7	2.7	12.0	24.0	Q1
CY74FCT652TQCT	SSOP	DBQ	24	2500	330.0	16.4	6.5	9.0	2.1	8.0	16.0	Q1

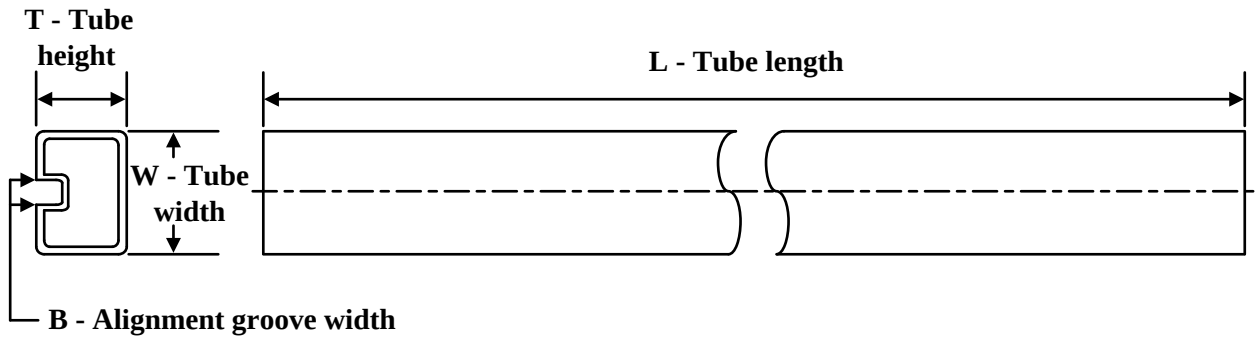
TAPE AND REEL BOX DIMENSIONS



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CY74FCT652ATQCT	SSOP	DBQ	24	2500	356.0	356.0	35.0
CY74FCT652ATSOCT	SOIC	DW	24	2000	350.0	350.0	43.0
CY74FCT652CTQCT	SSOP	DBQ	24	2500	356.0	356.0	35.0
CY74FCT652CTSOCT	SOIC	DW	24	2000	350.0	350.0	43.0
CY74FCT652TQCT	SSOP	DBQ	24	2500	356.0	356.0	35.0

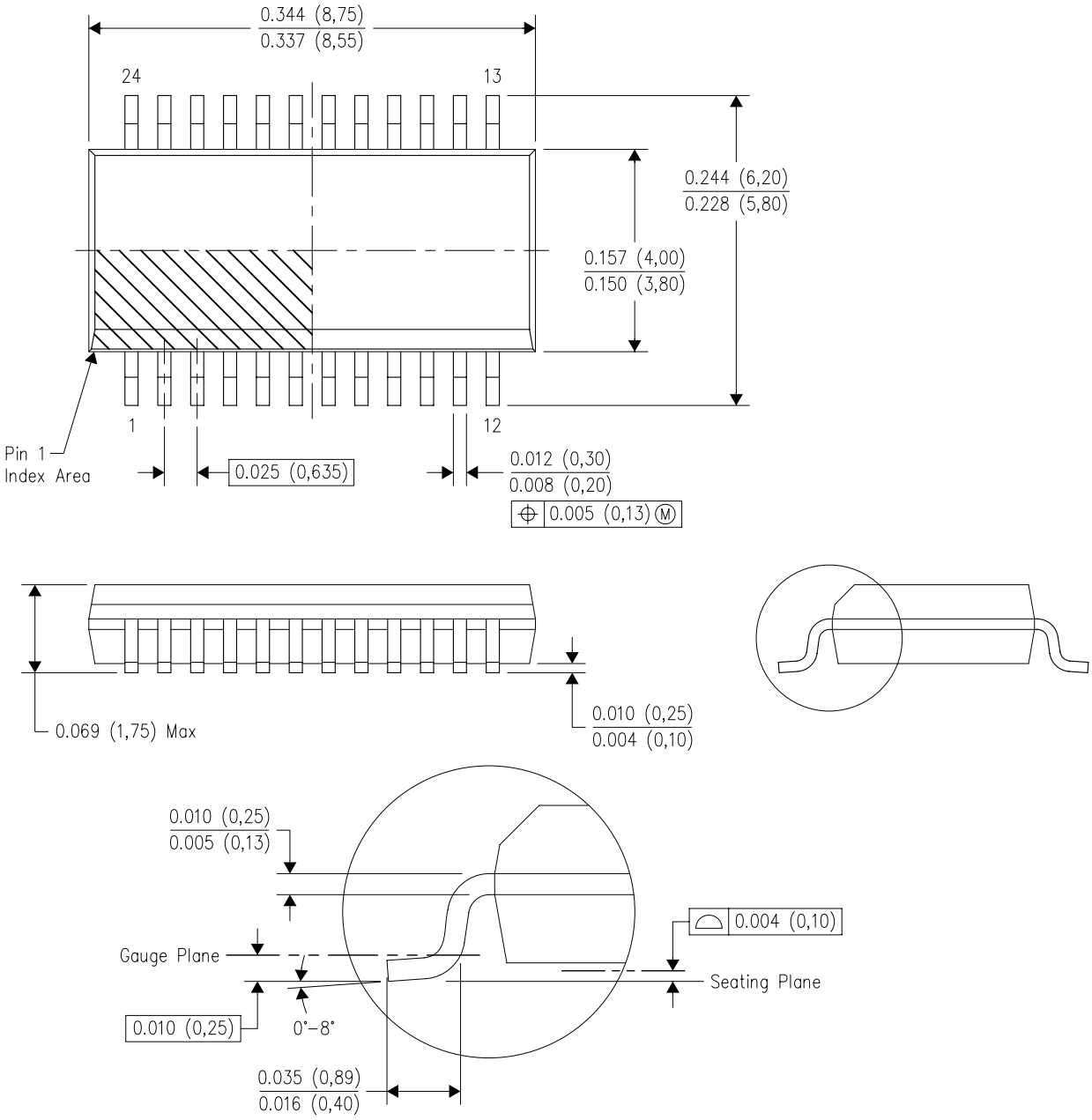
TUBE



*All dimensions are nominal

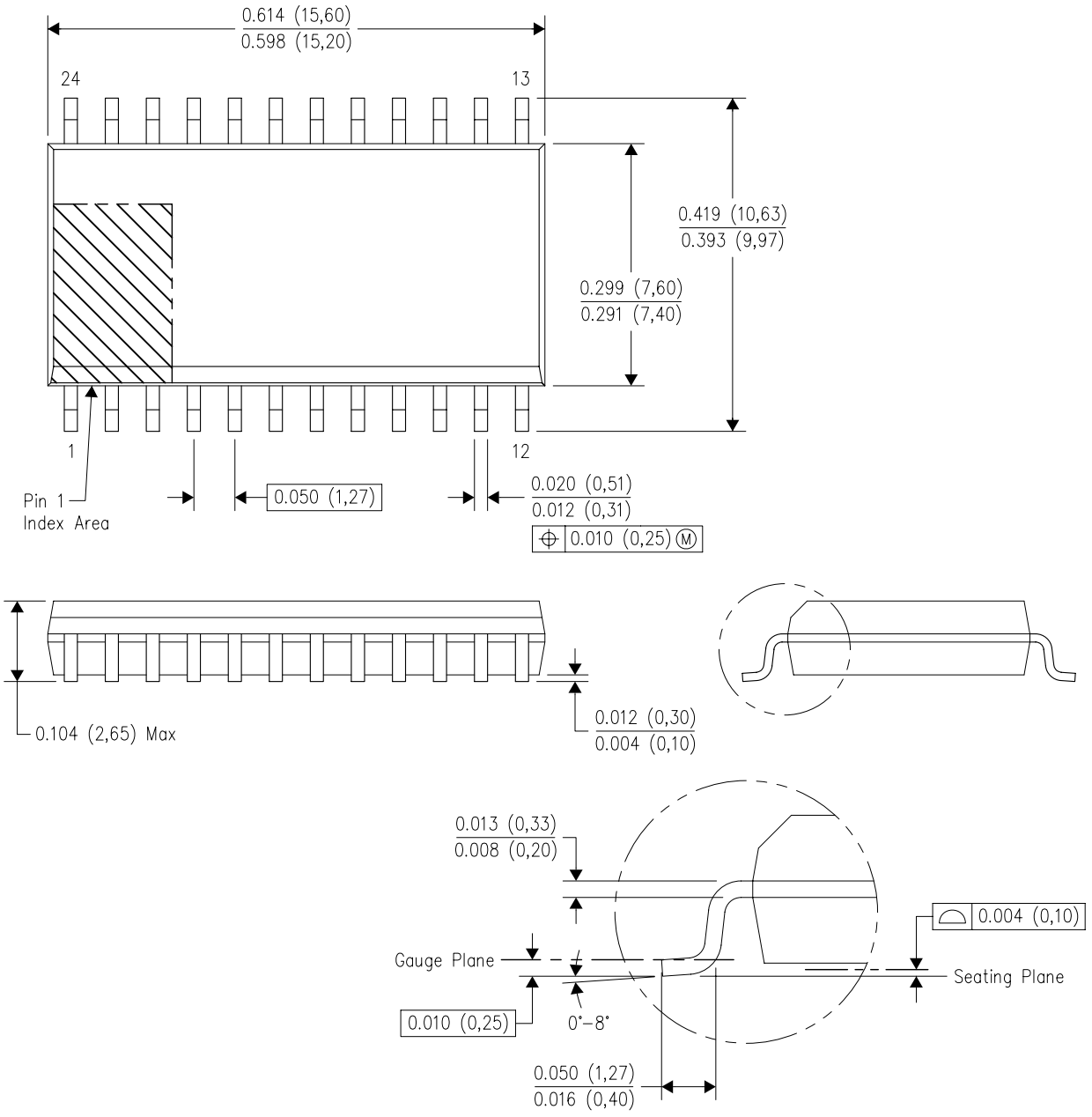
Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	T (µm)	B (mm)
CY74FCT652ATSOC	DW	SOIC	24	25	506.98	12.7	4826	6.6
CY74FCT652ATSOC.B	DW	SOIC	24	25	506.98	12.7	4826	6.6

DBQ (R–PDSO–G24) PLASTIC SMALL–OUTLINE PACKAGE



NOTES:
A. All linear dimensions are in inches (millimeters).
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15) per side.
D. Falls within JEDEC MO–137 variation AE.

DW (R–PDSO–G24) PLASTIC SMALL OUTLINE



NOTES:
A. All linear dimensions are in inches (millimeters). Dimensioning and tolerancing per ASME Y14.5M–1994.
B. This drawing is subject to change without notice.
C. Body dimensions do not include mold flash or protrusion not to exceed 0.006 (0,15).
D. Falls within JEDEC MS–013 variation AD.

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